

<b>INFORMATION DISCLOSURE CITATION PTO-1449</b>	Atty. Docket No. <b>990342A</b>	Serial No. <b>Not Yet Assigned</b>
	Applicant(s): <b>SHIMOYAMA, et al.</b>	
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#### U.S. PATENT DOCUMENTS

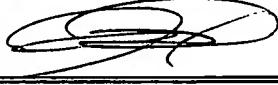
Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
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	AB	5,465,266	Bour et al.	11/1995		
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	AE	EP 0 469 301	6/29/90	European
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	AG	LIN J-F ET AL: "High temperature and low threshold current operation of strained AlGaInP/Ga0.4In0.6P multiple quantum well laser diodes emitting at 676 nm" vol. 30, no. 6, pages 494-495, March 1994.
	AH	Patent Abstracts of Japan; vol. 017, no. 065 (E-1317); February 9, 1993 & JP 04 269886 A (Toshiba Corp.), 9/25/92.
	AI	Patent Abstracts of Japan; vol. 1997, no. 11, November 28, 1997 & JP 09 199791 A (NNEC Corp), July 31, 1997

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